

MMBTA92

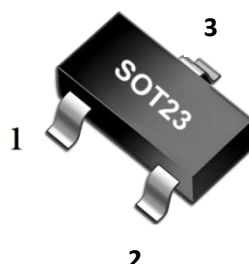
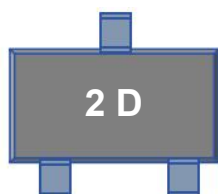
PNP SILICON TRANSISTOR

FEATURES

*High voltage transistor

MARKING

Type Code: Marking: 2 D



1. BASE
2. EMITTER
3. COLLECTOR

ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-base voltage	-300	V
V _{CEO}	Collector-emitter voltage	-300	V
V _{EB0}	Emitter-base voltage	-5	V
I _C	Collector current	-200	mA
I _{CM}	Collector Current -Pulsed	500	mA
P _C	Collector Power Dissipation	300	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-60~150	°C
R _{θJA}	Thermal Resistance From Junction To Ambient	417	°C/W

ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

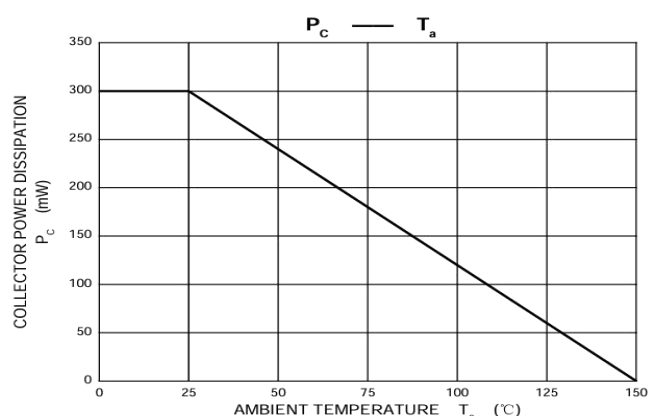
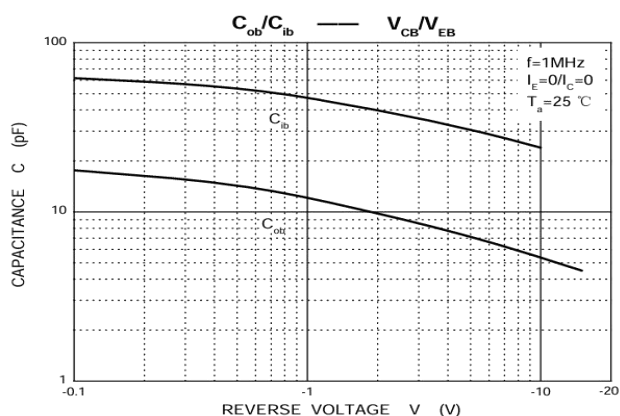
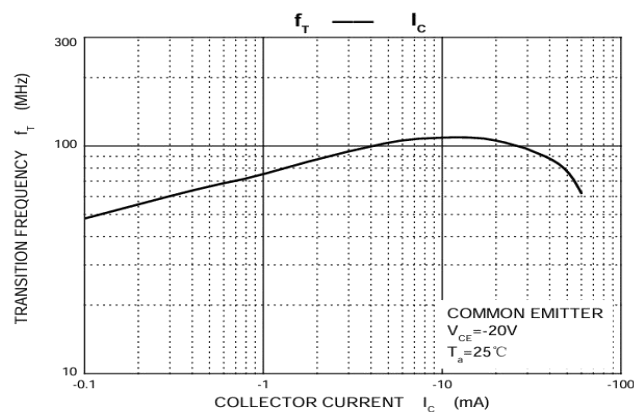
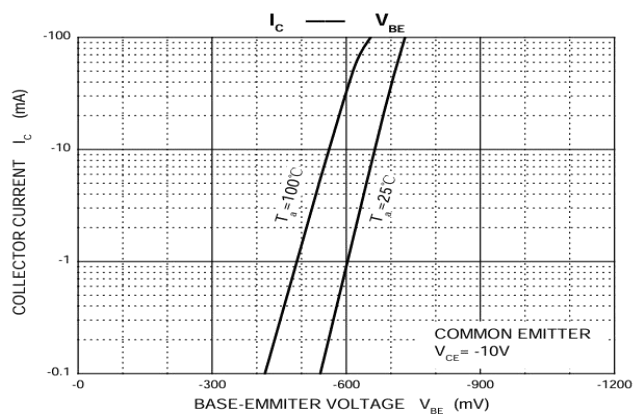
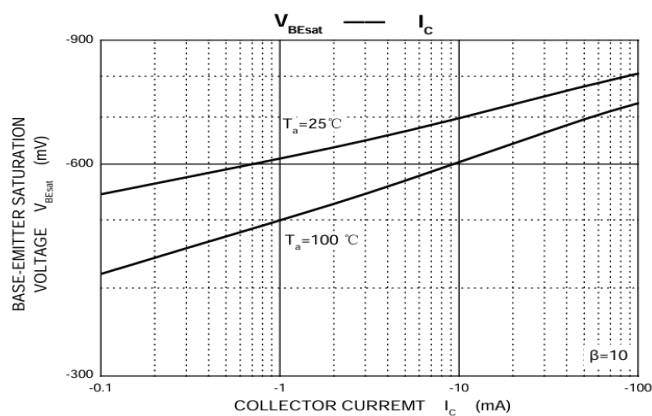
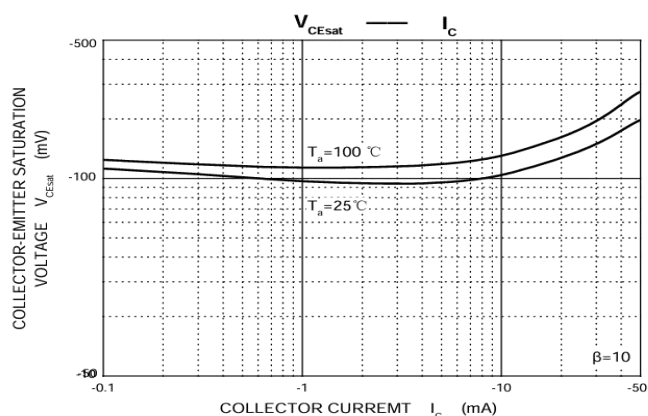
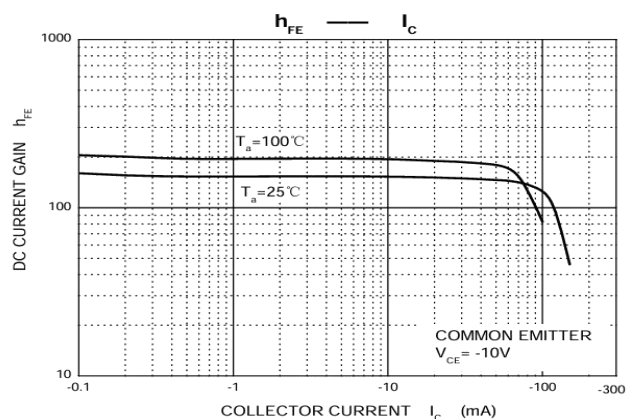
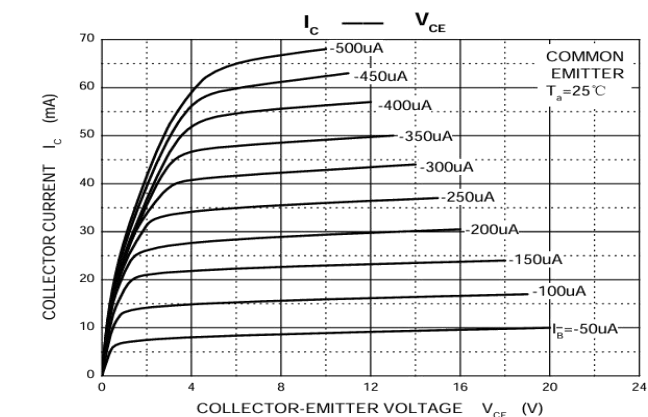
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-300		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-300		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5		V
Collector cutoff current	I _{CB0}	V _{CB} =-200V, I _E =0		-0.25	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0		-0.1	μA
DC Current Gain	h _{FE1}	V _{CE} =-10V, I _C =-1mA	60		
	h _{FE2}	V _{CE} =-10V, I _C =-10mA	100	200	
	h _{FE3}	V _{CE} =-10V, I _C =-30mA	60		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20mA, I _B =-2mA		-0.2	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-20mA, I _B =-2mA		-0.9	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-100mA, f=30MHz	50		MHz



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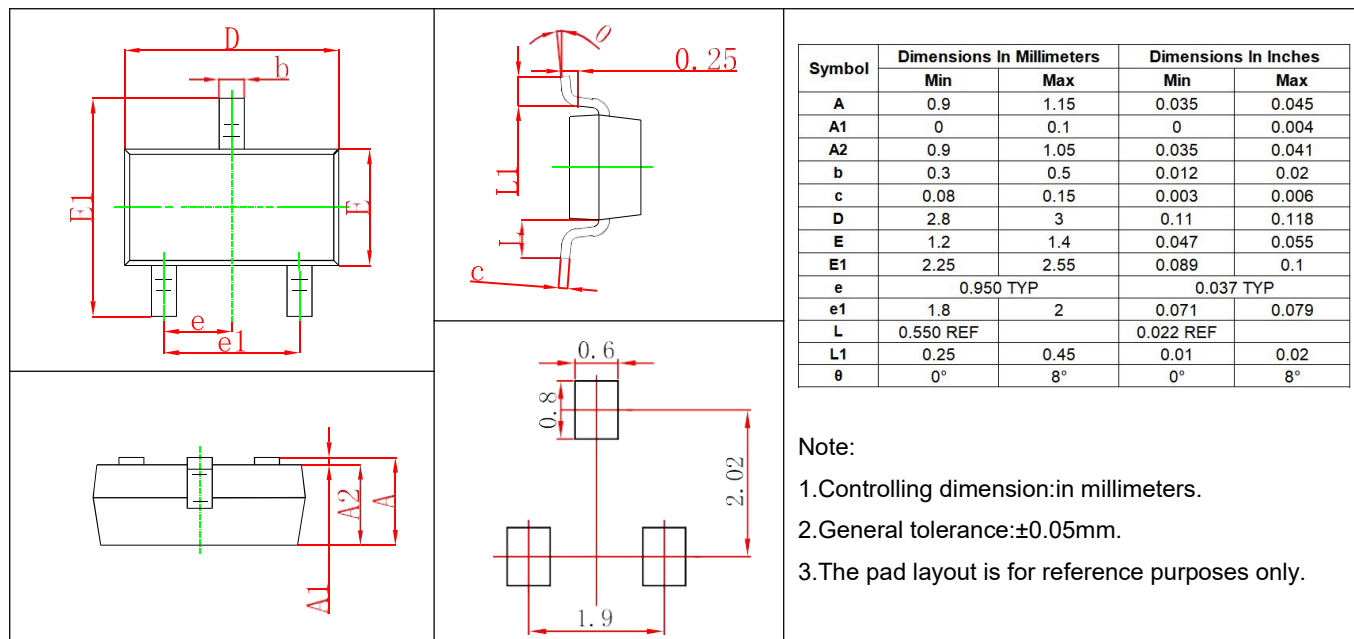
TYPICAL CHARACTERISTICS



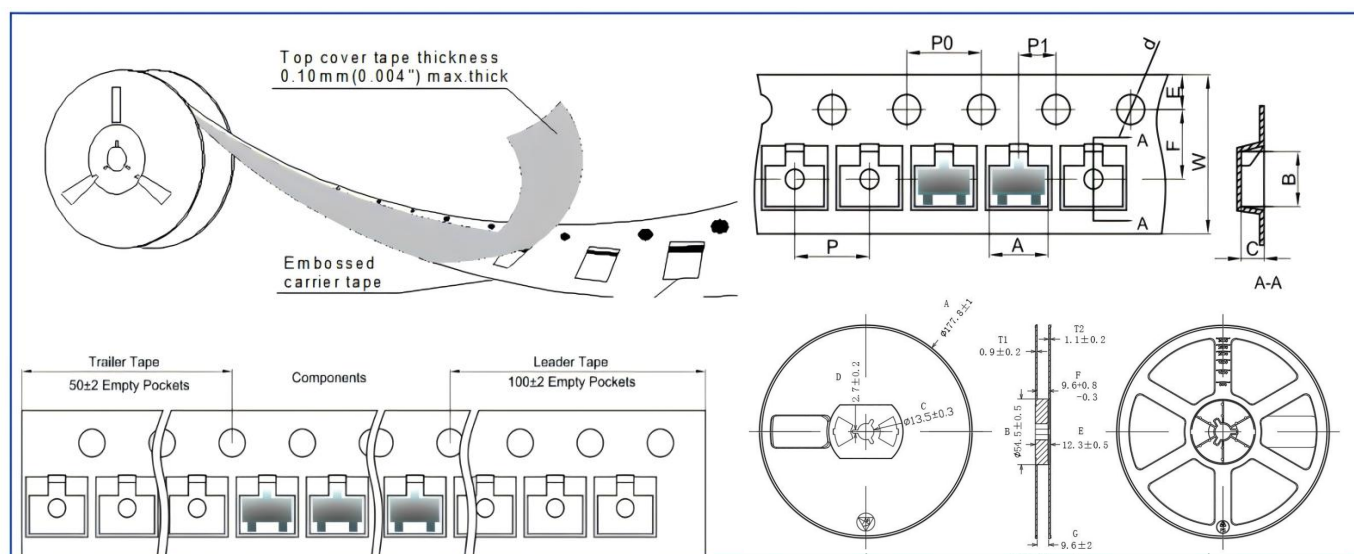
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SOT23 PACKAGE OUTLINE DIMENSIONS



REEL PACKING



Dimensions are in millimeter										
PKG TYPE	A	B	C	d	E	F	Po	P	P1	W
SOT-23	3.17	2.77	1.22	Φ1.55	1.75	3.50	4.00	4.00	2.00	8.00
Reel Option	A	B	C	D	E	F	G	T1	T2	Q.TY PER REEL
7" Dia	Φ177.8	Φ54.5	Φ13.5	2.7	12.3	9.6	9.6	0.9	1.1	3000PCS